Figure 1: Thickness versus cycle (a,c) and selectivity (b,d) on blanket SiN and SiO_2 surfaces exposed to $TiCl_4$/$Ti(^iPrO)_4$ ALD after: (a,b) a dilute HF dip; and (c,d) a dilute HF dip followed by MoF_6 for 1 second. The lines correspond to fits to an analytical nucleation model.[4] The selectivity is determined from the difference between the TiO_2 surface coverage on the growth and non-growth surface, divided by the sum of the coverages. The lines correspond to the data fits, and the dots correspond to values determined from the measured thickness values.